

Amendments to the Specification

Please amend page 11, paragraph 25 in the following manner:

[0025] In lithography, focus and exposure are two process parameters that have a great impact on patterning of devices and therefore ~~they are~~ monitoring and controlling focus and exposure is important. Each of these parameters ~~[[e]]~~ affects the formation of patterns including grating structures in a non trivial way. The grating structures therefore can be specially designed to monitor focus and exposure. The grating structures may for example include different grating parameters that were formed differently because of different sensitivities to focus and/or exposure, i.e., change depending on focus and exposure. By way of example, a first grating structure may include a first parameter having a first value formed from a first sensitivity to focus (and/or exposure) and a second grating structure may include a first parameter having a second value formed from a second sensitivity to focus (and/or exposure). The second sensitivity may be greater or less than the first sensitivity to focus (and/or exposure). This example set may include additional grating structures, which have different sensitivities to focus (and/or exposure) in order to obtain more pieces of information about focus (and/or exposure). Additional sets of grating structure sets may also be used to obtain even more information. For example, a second set of grating structures more sensitive to the other process parameters such as exposure may be used. In one particular embodiment, focus is monitored with grating structures having different line widths that were affected differently by the sign and magnitude of focus. As mentioned above, linewidth is one parameter that is highly sensitive to focus.